EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L3	1	"63237571".pn.	JPO	OR	OFF	2009/11/03 14:11
S14	856	349/138	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 10:35
S15	990	349/122	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 10:35
S16	654	349/158	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 10:35
S17	1861	349/43	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 10:36
S21	3	"5051570".pn. "4007294". pn. "5268679".pn.	USPAT	OR	ON	2006/01/23 11:20
S22	180	(level$4 flat$6) with organic with (TFT (thin adj fim adj transistor))	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 10:51
S23	2	"5162901".pn.	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 10:40
S24	241	(level$4 flat$6) with organic with (TFT (thin adj fim adj transistor))	US-PGPUB	OR	ON	2006/01/23 10:49

S25	0	(level$4 flat$6) with organic with (TFT (thin adj fim adj transistor)) and "19950117".ad.	US-PGPUB	OR	ON	2006/01/23 10:51
S26	0	(level$4 flat$6) with organic with (TFT (thin adj fim adj transistor)) and "19950117".ad.	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 10:52
S27	1	(level$4 flat$6) and organic and (TFT (thin adj fim adj transistor)) and "19950117".ad.	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 10:53
S28	2	(level$4 flat$6) with organic with (TFT (thin adj fim adj transistor)) and @ad<"19950117"	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 10:59
S29	1	"5414442".pn.	USPAT	OR	ON	2007/06/20 13:53
S30	2	(level$4 flat$6) with organic with (TFT (thin adj fim adj transistor)) and @ad<"19950117"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 11:00
S31	2701	(transparent with pixel) and @ad<"19950117"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 11:33
S32	1693	((transparent with pixel) and @ad<"19950117") and (liquid adj crystal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 11:33
S33	322	((transparent with pixel) and @ad<"19950117") and (liquid adj crystal) and (gate adj insulat$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 11:43
S34	5	((transparent with pixel) and @ad<"19950117") and (liquid adj crystal) and (gate adj insulat$4) and ((flat$5 level$4) with organic)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 11:35

S35	288	((transparent near10 pixel) and @ad<"19950117") and (liquid adj crystal) and (gate adj insulat$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 11:48
S36	161	((transparent near10 pixel) and @ad<"19950117") and (liquid adj crystal) and (gate adj insulat$4) and (level$4 flat$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/06 11:49
S37	30	((transparent near10 pixel) and @ad<"19950117") and (liquid adj crystal) and (gate adj insulat$4) and (level$4 flat$4) and (crystalline adj silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 12:58
S38	8	((transparent near10 pixel) and @ad<"19920218") and (liquid adj crystal) and (gate adj insulat$4) and (level$4 flat$4) and (crystalline adj silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 13:00
S39	1	((transparent near10 pixel) and @ad<"19920218") and (liquid adj crystal) and ((gate adj insulat$4) with fluor$4) and (level$4 flat$4) and (crystalline adj silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 13:01
S40	1	"20020033906".pn.	US-PGPUB	OR	ON	2006/01/23 16:06
S41	1	"5340999".pn.	USPAT	OR	ON	2006/06/08 11:24
S43	1	"63082177".pn.	JPO	OR	OFF	2007/03/06 10:21
S44	161	((transparent near10 pixel) and @ad<"19950117") and (liquid adj crystal) and (gate adj insulat$4) and (level$4 flat$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/20 10:40
S45	1396	((gate adj insulat$4) and @ad<"19950117") and (liquid adj crystal) and semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/20 10:42

S46	861	((gate adj insulat$4) near10 semiconductor) and @ad<"19950117" and (liquid adj crystal)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/20 10:43
S47	114	((gate adj insulat$4) near10 (semiconductor adj film)) and @ad<"19920218" and (liquid adj crystal)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/20 13:47
S48	125	((gate adj insulat$4) with (semiconductor adj film)) and @ad<"19920218" and (liquid adj crystal)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/31 14:37
S49	1	"5306651".pn.	USPAT	OR	ON	2007/06/20 13:55
S50	1	"5289030".pn.	USPAT	OR	ON	2007/06/20 13:55
S51	417	((gate adj insulat$4) with ((semiconductor adj film) silicon)) and @ad<"19920218" and (liquid adj crystal)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/31 14:37
S52	264	((gate adj insulat$4) with ((semiconductor adj film) silicon))and surface and @ad<"19920218" and (liquid adj crystal)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/31 14:38
S53	18	"5166816".pn. "4691995".pn. "4581620".pn. "5159476".pn. "5153142".pn. "4908710".pn. "5591987".pn. "4839707".pn. "5998841".pn. "5181132".pn. "20020033906".pn. "6778231".pn. "4704002".pn. "7115902".pn. "4487481".pn. "5119204".pn. "5257105".pn. "5300944".pn.	US-PGPUB; USPAT	OR	OFF	2008/01/16 10:27

S56	14	"6281520".pn. "6011277". pn. "6737676".pn. "5905555".pn. "5899547". pn. "5946059".pn. "7154147".pn. "6023075". pn. "7098479".pn. "7067844".pn. "6838698". pn. "7253437".pn. "6437367".pn. "6436815". pn.	USPAT	OR	ON	2008/05/23 09:38
S57	4	"20060151792".pn. "20070252149".pn. "20050001965".pn. "20050007329".pn.	US-PGPUB	OR	ON	2008/05/23 09:40
S58	105	((gate adj electrode) near10 (pixel adj electrode)) and @ad<"19920218"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/23 10:41
S61	1	"5054887".pn.	USPAT	OR	ON	2008/05/23 11:46
S62	644	(insulat$4 near10 (contact adj hole)near10 gate) and @ad<"19920218"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/13 10:04
S63	36	(insulat$4 near10 (contact adj hole) near10 gate) and (liquid adj crystal) and @ad<"19920218"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/13 10:05
S64	1	"20090021663".pn.	US-PGPUB; USPAT	OR	OFF	2009/05/04 11:48
S65	36	(insulat$4 near10 (contact adj hole) near10 gate) and (liquid adj crystal) and (@ad<"19920218" @ad="19920218")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/09/17 08:23
S66	358	((insulat$4 near10 (contact adj hole) near10 gate) and (liquid adj crystal)).clm.	US-PGPUB	OR	ON	2009/09/17 08:25
S67	344	((insulat$4 near10 (contact adj hole) near10 gate) and (liquid adj crystal) and (gate near10 contact)).clm.	US-PGPUB	OR	ON	2009/09/17 08:26

S68	85	((insulat$4 near10 (contact adj hole) near10 gate) and (liquid adj crystal) and (gate near10 contact near10 semiconductor)).clm.	US-PGPUB	OR	ON	2009/09/17 08:27
S70	19	"5306651".pn. "4772927".pn. "4470060".pn. "5008218".pn. "5166085".pn. "5017984".pn. "4762807".pn. "5159477".pn. "5083190".pn. "5164805".pn. "4651182".pn. "7420628".pn. "7479939".pn. "7423290".pn. "7489367".pn. "4682407".pn. "4740481".pn. "4997785".pn. "20090021663".pn.	US-PGPUB; USPAT	OR	OFF	2009/11/03 11:15

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